# **Complementary Silicon Plastic Power Transistors**

These devices are designed for use in general—purpose amplifier and switching applications.

#### **Features**

- High DC Current Gain
- High Current Gain Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant\*

#### MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N6487, 2N6490 2N6488, 2N6491	V <sub>CEO</sub>	60 80	Vdc
Collector–Base Voltage 2N6487, 2N6490 2N6488, 2N6491	V <sub>CB</sub>	70 90	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	15	Adc
Base Current	Ι <sub>Β</sub>	5.0	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	75 0.6	W W/°C
Total Power Dissipation  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.8 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

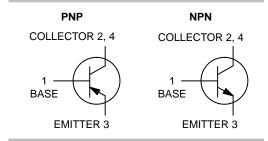
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	70	°C/W

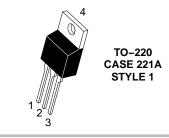


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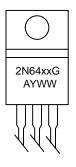
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# 15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60-80 VOLTS, 75 WATTS





#### MARKING DIAGRAM



2N64xx = Specific Device Code xx = See Table on Page 5 G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week

#### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information in the package dimensions section on page 5 of this data sheet.

<sup>1.</sup> Indicates JEDEC Registered Data.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>			
Collector–Emitter Sustaining Voltage (Note 3) (I <sub>C</sub> = 200 mAdc, I <sub>B</sub> = 0) 2N6487, 2N6490 2N6488, 2N6491	V <sub>CEO(sus)</sub>	60 80	- -	Vdc
Collector–Emitter Sustaining Voltage (Note 3) (I <sub>C</sub> = 200 mAdc, V <sub>BE</sub> = 1.5 Vdc) 2N6487, 2N6490 2N6488, 2N6491	V <sub>CEX</sub>	70 90	_ _	Vdc
Collector Cutoff Current $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$ 2N6487, 2N6490 $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$ 2N6488, 2N6491	I <sub>CEO</sub>	-	1.0 1.0	mAdc
Collector Cutoff Current $ \begin{array}{l} (\text{V}_{\text{CE}} = 65 \text{ Vdc}, \text{V}_{\text{EB(off)}} = 1.5 \text{ Vdc}) \\ 2\text{N}6487, 2\text{N}6490 \\ (\text{V}_{\text{CE}} = 85 \text{ Vdc}, \text{V}_{\text{EB(off)}} = 1.5 \text{ Vdc}) \\ 2\text{N}6488, 2\text{N}6491 \\ (\text{V}_{\text{CE}} = 60 \text{ Vdc}, \text{V}_{\text{EB(off)}} = 1.5 \text{ Vdc}, \text{T}_{\text{C}} = 150^{\circ}\text{C}) \\ 2\text{N}6487, 2\text{N}6490 \\ (\text{V}_{\text{CE}} = 80 \text{ Vdc}, \text{V}_{\text{EB(off)}} = 1.5 \text{ Vdc}, \text{T}_{\text{C}} = 150^{\circ}\text{C}) \\ 2\text{N}6488, 2\text{N}6491 \\ \end{array} $	I <sub>CEX</sub>	- - -	500 500 5.0 5.0	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	1.0	mAdc
ON CHARACTERISTICS	<u> </u>			
DC Current Gain ( $I_C = 5.0$ Adc, $V_{CE} = 4.0$ Vdc) ( $I_C = 15$ Adc, $V_{CE} = 4.0$ Vdc)	h <sub>FE</sub>	20 5.0	150 -	-
Collector–Emitter Saturation Voltage ( $I_C = 5.0$ Adc, $I_B = 0.5$ Adc) ( $I_C = 15$ Adc, $I_B = 5.0$ Adc)	VCE(sat)	<u>-</u> -	1.3 3.5	Vdc
Base–Emitter On Voltage ( $I_C = 5.0$ Adc, $V_{CE} = 4.0$ Vdc) ( $I_C = 15$ Adc, $V_{CE} = 4.0$ Vdc)	V <sub>BE(on)</sub>	- -	1.3 3.5	Vdc
DYNAMIC CHARACTERISTICS	<u> </u>			
Current-Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f <sub>test</sub> = 1.0 MHz)	f⊤	5.0	_	MHz
Small–Signal Current Gain ( $I_C = 1.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	h <sub>fe</sub>	25	_	_

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics for the listed test conditions performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Indicates JEDEC Registered Data. 3. Pulse Test: Pulse Width  $\leq 300~\mu s$ , Duty Cycle  $\leq 2.0\%$ . 4.  $f_T = |h_{fe}| \bullet f_{test}$ 

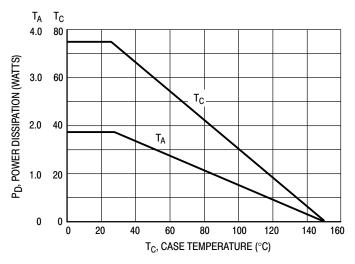
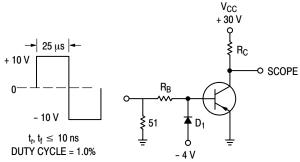


Figure 1. Power Derating



 $\rm R_B$  and  $\rm R_C$  varied to obtain desired current levels. For PNP, reverse all polarities.

D<sub>1</sub> MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I<sub>B</sub>  $\approx$  100 mA MSD6100 USED BELOW I<sub>B</sub>  $\approx$  100 mA

1000 500 200 t, TIME (ns) 100  $t_d \ @ \ V_{BE(off)} \approx 5.0 \ V$ 50 T<sub>C</sub> = 25°C 20  $V_{CC} = 30 \text{ V}$  $I_C/I_B = 10$ 10 \_\_\_\_ 0.5 2.0 20 IC, COLLECTOR CURRENT (AMP)

Figure 2. Switching Time Test Circuit

Figure 3. Turn-On Time

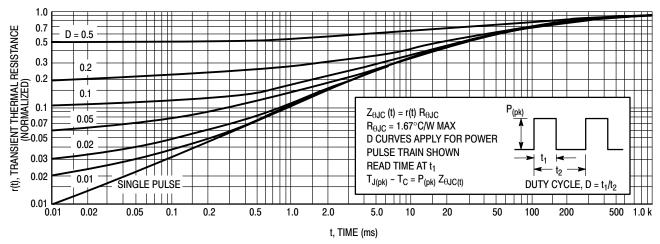


Figure 4. Thermal Response

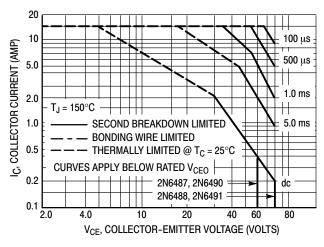


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistors average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

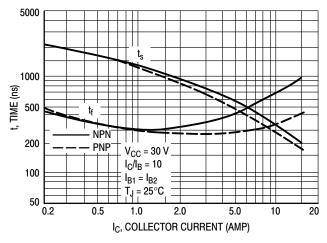


Figure 6. Turn-Off Time

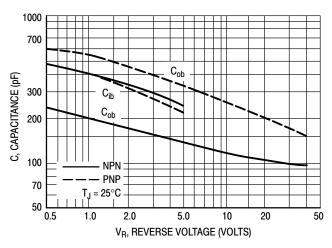
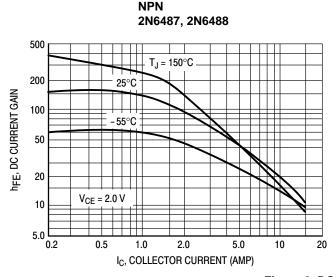


Figure 7. Capacitances



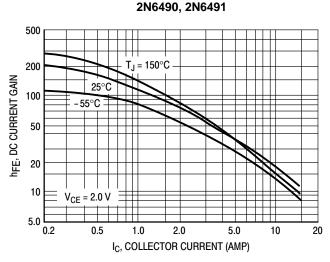
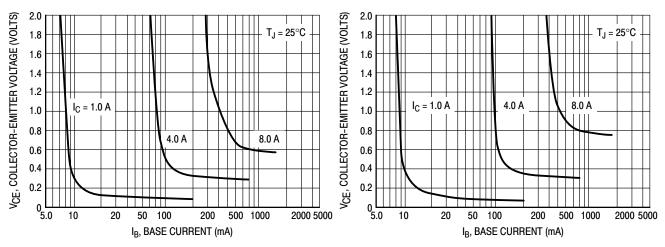


Figure 8. DC Current Gain



**Figure 9. Collector Saturation Region** 

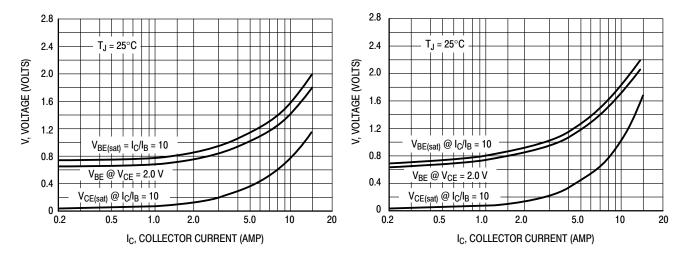
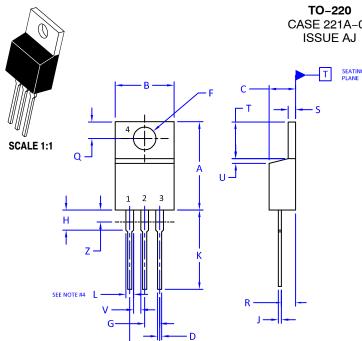


Figure 10. "On" Voltages

#### **ORDERING INFORMATION**

Device	Device Marking	Package	Shipping
2N6487G	2N6487	TO-220 (Pb-Free)	50 Units / Rail
2N6488G	2N6488	TO-220 (Pb-Free)	50 Units / Rail
2N6490G 2N6490		TO-220 (Pb-Free)	50 Units / Rail
2N6491G	2N6491	TO-220 (Pb-Free)	50 Units / Rail

## **MECHANICAL CASE OUTLINE**



CASE 221A-09

**DATE 05 NOV 2019** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11	:	STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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